General Description

The MAX1665 provides protection against overvoltage, undervoltage, overcharge current, and overdischarge current for 2-cell to 4-cell lithium-ion (Li+) battery packs. Very low operating current ensures that cells are not overdischarged during long storage periods.

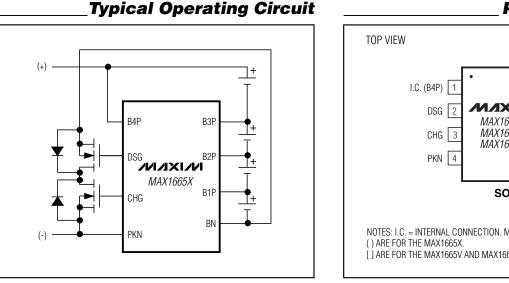
The MAX1665 controls two external N-channel MOSFETs to limit the charge and discharge voltages. Charging is allowed when the per-cell voltage is below +4.3V. When the voltage on any cell rises above +4.3V (overvoltage limit), the MAX1665 turns off the charge MOSFET. This safety feature prevents overcharge of any cell within the battery pack.

Discharge is allowed when the per-cell voltage is above +2.5V (undervoltage limit). If the voltage across any cell falls below +2.5V, the MAX1665 turns off the discharge MOSFET. This safety feature prevents overdischarge of any cell within the battery pack.

Charging and discharging are allowed if the voltage between PKN and BN is less than 250mV. This safety feature prevents excessive pack current.

Applications

Lithium-Ion Battery Packs



MIXIM

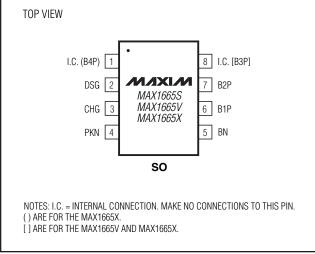
Features

- Complete Protection Against: **Cell Overvoltage Cell Undervoltage**
- Pack Protection for Excessive Charge and Discharge
- Very Low Supply Current: 16µA typ
- Low Standby Current: 1µA max
- Matched Cell Input Bias Current (<500pA) **Preserves Cell Balance**

Ordering Information

| PART | TEMP. RANGE | PIN- PACKAGE | CELL COUNT |
|-------------|----------------|-----------------|---------------|
| MAX1665SESA | -40°C to +85°C | 8 SO | 2 |
| MAX1665VESA | -40°C to +85°C | 8 SO | 3 |
| MAX1665XESA | -40°C to +85°C | 8 SO | 4 |

Pin Configuration



Maxim Integrated Products 1

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ABSOLUTE MAXIMUM RATINGS

| B4P to PKN (MAX1665X) | 0.3V to +24V |
|--------------------------------|-----------------------------------|
| B3P to PKN (MAX1665V) | 0.3V to +18V |
| B2P to PKN (MAX1665S) | 0.3V to +12V |
| B1P to PKN, B2P to B1P, B3P to | B2P, B4P to B3P0.3V to +6V |
| CHG to PKN, DSG to BN | |
| MAX1665S | 0.3V to $(V_{B2P} + 0.3V)$ |
| MAX1665V | 0.3V to (V _{B3P} + 0.3V) |
| MAX1665X | 0.3V to $(V_{B4P} + 0.3V)$ |
| B2P to BN (MAX1665S) | 0.3V to +12V |

| B3P to BN (MAX1665V) | |
|---|----------------|
| B4P to BN (MAX1665X) | 0.3V to +24V |
| Continuous Power Dissipation (T_A = +70°C) | |
| 8-Pin SO (derate 5.88mW/°C above +70° | °C)471mW |
| Operating Temperature Range | 40°C to +85°C |
| Junction Temperature | +150°C |
| Temperature Range | 65°C to +150°C |
| Lead Temperature (soldering, 10s) | +300°C |

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{B2P} = 8V (MAX1665S), V_{B3P} = 12V (MAX1665V), V_{B4P} = 16V (MAX1665X), T_A = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)$

| PARAMETER | SYMBOL | COND | ITIONS | MIN | ТҮР | MAX | UNITS |
|-------------------------------------|------------------|--|------------------------------|------------------------|------|-----------------------|-------|
| B2P Voltage Range | V _{B2P} | MAX1665S | | 4 | | 10 | V |
| B3P Voltage Range | V _{B3P} | MAX1665V | | 4 | | 15 | V |
| B4P Voltage Range | V _{B4P} | MAX1665X | | 4 | | 20 | V |
| Overvoltage Threshold | Vov | Cell voltage rising | | 4.26 | 4.3 | 4.34 | V |
| Overvoltage Hysteresis | VCE | | | | 0.10 | | V |
| Undervoltage Threshold | VUV | | | 2.4 | 2.5 | 2.6 | V |
| Undervoltage RESET | V _{RE} | V _{BN} - V _{PKN} | | 0 | 18 | 30 | mV |
| Overcurrent Sense Threshold | VCH | | | ±200 | ±250 | ±300 | mV |
| Overcurrent Hysteresis | VCH2 | | | | 5 | | mV |
| Overvoltage/Undervoltage Delay | t _{UV} | (Note 1) | | | 200 | | ms |
| Overcurrent Detection Delay | t _{IO} | | | | 10 | | ms |
| | | | MAX1665S | V _{B2P} - 1.8 | 3 Ve | _{32P} - 0.54 | |
| CHG, DSG Output Voltage High | | Ι _{ΟUT} = 100μΑ | MAX1665V | V _{B3P} - 1.8 | 3 Ve | 33P - 0.54 | V |
| | | | MAX1665X | V _{B4P} - 1.8 | 3 Ve | _{34P} - 0.54 | |
| DSG Output Voltage High (Note 2) | | MAX1665X, I _{OUT} = 10 V _{BN} = 100mV | $0\mu A, V_{B4P} = 24V,$ | | 17 | 20 | V |
| CHG Output Voltage Low | VCHGL | I _{CHG} = -100µА | | | VF | ^р КN + 0.1 | V |
| DSG Output Voltage Low | VDSGL | I _{DSG} = -1µA | | | ١ | / _{BN} + 0.1 | V |
| CHG, DSG Output Source Current | ЮН | CHG = PKN, DSG = B | Ν | 10 | 25 | | mA |
| CHG Output Sink Current | IOL | V _{CHG} = V _{PKN} + 3.0V | | 0.5 | 2 | | mA |
| DSG Output Sink Current | IOL | $V_{DSG} = V_{BN} + 3.0V$ | | | 2 | | μA |
| Overcurrent Sampling - tON | ton | $V_{PKN} = \pm 300 \text{mV}$ | | | 8.2 | | ms |
| Overcurrent Sampling - tOFF | tOFF | $V_{PKN} = \pm 300 \text{mV}$ | | | 135 | | ms |
| | | MAX1665SESA, V _{B1P} | = 4V | | 3 | 10 | nA |
| Input Pige Current (Note 2) | Inua | MAX1665VESA, VB1P | = 4V, V _{B2P} = 8V | | 3 | 10 | |
| Input Bias Current (Note 3) | IBIAS | MAX1665XESA, V_{B1P} $V_{B3P} = 12V$ | = 4V, V _{B2P} = 8V, | | 3 | 10 | nA |



ELECTRICAL CHARACTERISTICS (continued)

 $(V_{B2P} = 8V (MAX1665S), V_{B3P} = 12V (MAX1665V), V_{B4P} = 16V (MAX1665X), T_A = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.)$

| PARAMETER | SYMBOL | CONDITIONS | MIN | TYP | MAX | UNITS |
|-----------------------------|-------------------|-----------------|-----|------|-----|-------|
| Input Bias Current Matching | ΔI_{BIAS} | (Notes 3, 4) | | ±500 | | рА |
| Supply Current | Icc | | | 16 | 25 | μA |
| Standby Mode Current | ILP | (Note 5) | | 0.7 | 1 | μA |
| Undervoltage Lockout | Vuvlo | DSG = CHG = low | | 4.0 | 4.7 | V |

ELECTRICAL CHARACTERISTICS

(V_{B2P} = 8V (MAX1665S), V_{B3P} = 12V (MAX1665V), V_{B4P} = 16V (MAX1665X), T_A = -40°C to +85°C, unless otherwise noted.) (Note 6)

| PARAMETER | SYMBOL | CON | DITIONS | MIN | TYP MAX | UNITS | |
|-------------------------------------|------------------|---|--|----------------------|------------------------|------------|--|
| B2P Voltage Range | V _{B2P} | MAX1665S | | 4 | 10 | V | |
| B3P Voltage Range | V _{B3P} | MAX1665V | | 4 | 15 | V | |
| B4P Voltage Range | V _{B4P} | MAX1665X | | 4 | 20 | V | |
| Overvoltage Threshold | Vov | Cell voltage rising | | 4.20 | 4.24 | V | |
| Undervoltage Threshold | VUV | | | 2.4 | 2.6 | V | |
| Undervoltage RESET | V _{RE} | V _{BN} - V _{PKN} | | 0 | 30 | mV | |
| Overcurrent Sense Threshold | VCH | | | ±180 | ±320 | mV | |
| | | | MAX1665S | V _{B2P} - 2 | V _{B2P} - 0.5 | | |
| CHG, DSG Output Voltage High | | Ι _{ΟUT} = 100μΑ | MAX1665V | V _{B3P} - 2 | V _{B3P} - 0.5 | V | |
| | | | MAX1665X | V _{B4P} - 2 | V _{B4P} - 0.5 | | |
| DSG Output Voltage High (Note 2) | | MAX1665X, $I_{OUT} = 10$ V _{BN} = 100mV | $00\mu A, V_{B4P} = 24V,$ | | 20 | V | |
| CHG Output Voltage Low | VCHGL | I _{CHG} = -100µА | I _{СНG} = -100µА | | V _{PKN} + 0.1 | V | |
| DSG Output Voltage Low | VDSGL | I _{DSG} = -1µA | | | V _{BN} + 0.1 | V | |
| CHG, DSG Output Source Current | Іон | CHG = PKN, DSG = I | BN | 10 | | mA | |
| CHG Output Sink Current | IOL | $V_{CHG} = V_{PKN} + 0.3V$ | | 0.2 | | mA | |
| DSG Output Sink Current | I _{OL} | $V_{DSG} = V_{BN} + 0.3V$ | | 0.2 | | μA | |
| | | MAX1665SESA, VB1P | • = 4V | | 10 | | |
| Input Diag Current (Note 2) | | MAX1665VESA, VB1P | MAX1665VESA, $V_{B1P} = 4V$, $V_{B2P} = 8V$ | | 10 | ~ ^ | |
| Input Bias Current (Note 3) | IBIAS | MAX1665XESA, V_{B1P} $V_{B3P} = 12V$ | $v = 4V, V_{B2P} = 8V,$ | | 10 | nA | |
| Supply Current | Icc | | | | 30 | μA | |
| Standby Mode Current | I _{LP} | (Note 5) | | | 2 | μA | |
| Undervoltage Lockout | VUVLO | DSG = CHG = low | | | 4.7 | V | |

Note 1: Applies to the differential voltage measured on any cell.

Note 2: DSG is internally clamped to a maximum of 20V to protect the external MOSFET (VGS).

Note 3: Guaranteed by design.

Note 4: The input bias matching between cells is measured with a 4V voltage between cells.

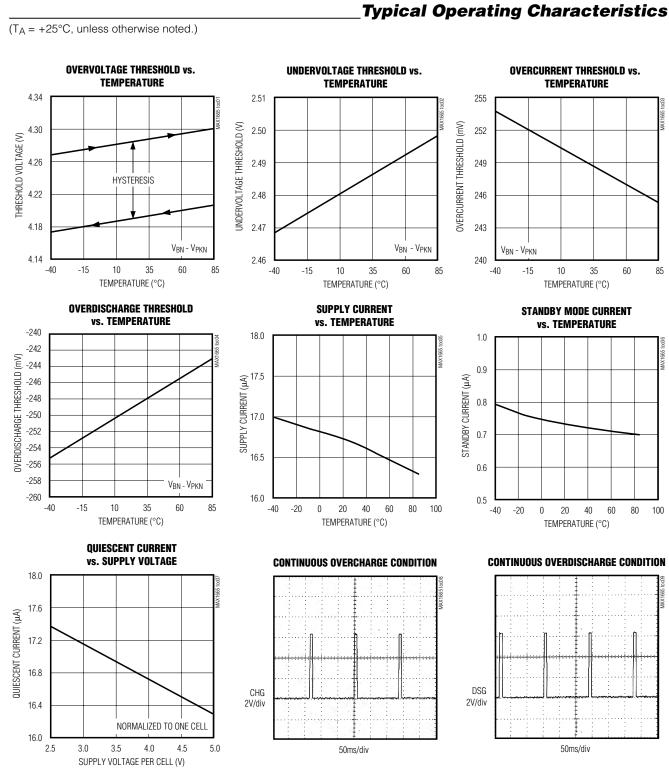
Note 5: At least one cell is $<V_{UV}$.

Note 6: Specifications to -40°C are guaranteed by design, not production tested.



MAX1665S/V/X

4



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Pin Description

| | PIN | | NAME | FUNCTION |
|----------|----------|----------|------|--|
| MAX1665S | MAX1665V | MAX1665X | | FUNCTION |
| 1, 8 | 1 | _ | I.C. | Internally Connected. Make no connection to this pin. |
| | _ | 1 | B4P | Cell 4 Positive Input. Connect to the positive terminal of the fourth series Li+ cell. |
| 2 | 2 | 2 | DSG | Discharge Control Output. Drives the gate of an external N-channel MOSFET to control the discharge path. |
| 3 | 3 | 3 | CHG | Charge Control Output. Drives the gate of an external N-channel MOSFET to control the charge path. |
| 4 | 4 | 4 | PKN | Pack Negative Input |
| 5 | 5 | 5 | BN | Connect to the negative terminal of the first series Li+ cell. |
| 6 | 6 | 6 | B1P | Cell 1 Positive Input. Connect to the positive terminal of the first series Li+ cell. |
| 7 | 7 | 7 | B2P | Cell 2 Positive Input. Connect to the positive terminal of the second series Li+ cell. |
| _ | 8 | 8 | B3P | Cell 3 Positive Input. Connect to the positive terminal of the third series Li+ cell. |

Table 1. Functionality Truth Table for VBN < VPKN + 0.018V (Discharge Mode)

| CHARGE OVERCURRENT | DISCHARGE OVERCURRENT | OVERVOLTAGE | UNDERVOLTAGE | CHG | DSG | GATE CLOCKED | MAX SUPPLY CURRENT* (µA) |
|-----------------------|--------------------------|-------------|--------------|-------|-------|-----------------|-----------------------------------|
| 0 | 0 | 0 | 0 | High | High | No | 25 |
| 0 | 0 | 0 | 1 | Low | Low | No | 1 |
| 0 | 0 | 1 | 0 | Low | High | No | 25 |
| 0 | 0 | 1 | 1 | Low | Low | No | 1 |
| 0 | 1 | 0 | 0 | Gated | Gated | Yes | 25 |
| 0 | 1 | 0 | 1 | Low | Low | No | 1 |
| 0 | 1 | 1 | 0 | Low | Gated | Yes | 25 |
| 0 | 1 | 1 | 1 | Low | Low | No | 1 |

*Assuming no load on CHG or DSG.

MAX1665S/V/X

| CHARGE OVERCURRENT | DISCHARGE OVERCURRENT | OVERVOLTAGE | UNDERVOLTAGE | CHG | DSG | GATE CLOCKED | MAX SUPPLY CURRENT* (µA) |
|-----------------------|--------------------------|-------------|--------------|-------|-------|-----------------|-----------------------------------|
| 0 | 0 | 0 | 0 | High | High | No | 25 |
| 0 | 0 | 0 | 1 | High | High | No | 25 |
| 0 | 0 | 1 | 0 | Low | High | No | 25 |
| 0 | 0 | 1 | 1 | Low | High | No | 25 |
| 1 | 0 | 0 | 0 | Gated | Gated | Yes | 25 |
| 1 | 0 | 0 | 1 | Gated | Gated | Yes | 25 |
| 1 | 0 | 1 | 0 | Low | High | No | 25 |
| 1 | 0 | 1 | 1 | Low | High | No | 25 |

Table 2. Functionality Truth Table for VBN > VPKN + 0.018V (Charge Mode)

*Assuming no load on CHG or DSG.

MAX1665S/V/X

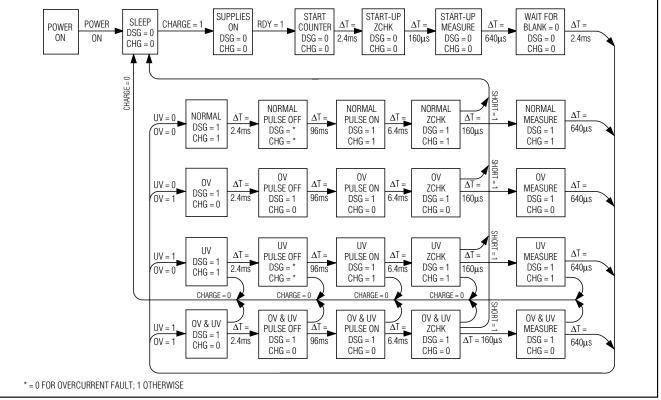


Figure 1. State Diagram

Detailed Description

The MAX1665S, MAX1665V, and MAX1665X supervise the charging and discharging processes on Li+ cells. Designed for 2, 3, and 4-cell applications, these devices monitor the voltage across each cell to provide protection against overcurrent, overvoltage, and undervoltage. Figure 1 shows the MAX1665 state diagram. Two control pins, CHG and DSG, drive the gates of two seriesconnected external N-channel MOSFETs, enabling/ disabling the charging/discharging process as necessary (see *Typical Operating Circuit*). The voltages at B1P, B2P, B3P, and B4P are measured differentially



across each cell to determine if the voltage levels are within operating range.

As depicted in the typical operating circuit, when CHG and DSG are high, the MOSFETs are on, allowing the cells to charge or discharge. However, when the charge or discharge current becomes excessive, the device turns off the FETs, enters a standby mode, and periodically samples the current to determine if the fault condition is removed. The MAX1665 does not sample the current directly, but rather measures the differential voltage across BN and PKN produced by the charge or discharge current flowing through the drain-to-source resistance of the MOSFETs. A preset voltage threshold is used to prevent excess current flow (see *Electrical Characteristics*).

In operating mode, all of the MAX1665 versions consume less than $25\mu A$ of quiescent current, allowing long-term battery storage without significantly affecting battery life. In standby mode, these devices consume less than $1\mu A$ of quiescent current.

Overvoltage Protection

When any individual cell voltage rises above Vov (overvoltage limit), the charge MOSFET control pin (CHG) is driven to PKN, thereby disconnecting the charger from the cells. The MAX1665 measures each cell of the pack differentially to prevent overcharging on a cell-by-cell basis. The charging process resumes when the highest cell voltage drops below Vov - 100mV (see *Typical Operating Circuit*).

Undervoltage/Overdischarge Protection Discharge can occur whenever the voltage of each cell is above the undervoltage threshold voltage (V_{UV}, typically 2.50V). If the voltage on any of the cells falls below V_{UV}, CHG latches to PKN and DSG latches to BN. Quiescent current falls to under 1 μ A as the device enters the standby mode. The latch resets when BN exceeds PKN by 18mV.

During charge mode, when BN is greater than PKN, the latch is held in reset, which disables the undervoltage comparator feature and allows charging on the cells. During the initialization process, as cells are connected to the MAX1665, the device considers this a low-voltage condition and disables CHG and DSG until a charging source is applied to create at least an 18mV differential between BN and PKN.

During long-term storage, the battery will self-discharge until it reaches the undervoltage threshold. When this happens, the MAX1665 enters standby mode. Normal operating mode resumes when a charger is connected, causing BN to rise 18mV above PKN.



When the MAX1665 detects overcurrent in the system, it disables the charge or discharge process by connecting CHG to PKN and DSG to BN, turning off the external MOSFETs (see *Typical Operating Circuit*). In charge mode, the MAX1665 detects overcharge when the voltage from BN to PKN exceeds +250mV. In discharge mode, overdischarge occurs when the differential voltage is less than -250mV. During any overcurrent condition, CHG and DSG are gated at 12Hz until the overcurrent is removed.

If both an overvoltage and overcharge condition exist, the overvoltage condition takes priority. Likewise, if undervoltage and overdischarge conditions exist, the overdischarge condition takes priority. For more details, see Tables 1 and 2.

Cell Current Balancing

When the battery cells are matched, the MAX1665 draws zero current from the intermediate nodes. The MAX1665 draws current from the top terminal only. Figure 2 shows a simplified diagram of the voltage sampling scheme. The following equations show that, for balanced cells, the differential discharge currents are zero:

B4P: $I_4 = 3I_{CB} + V_4 / R = 4V_4 / R = BAT4$ current B3P: $I_3 = I_{3P} + I_4 = BAT3$ current

$$I_{3P} + I_{CB} = V_3 / R \implies I_{3P} = V_3 / R - V_4 / R$$

$$_{3} = I_{4} + (V_{3} - V_{4}) / R = (3V_{4} + V_{3}) / R$$

B2P:
$$I_2 = I_{2P} + I_3 = BAT2 \text{ current}$$

 $I_{2P} + I_{CB} = V_2 / R \implies I_{2P} = V_2 / R - V_4 / R$
 $I_2 = I_3 + V_2 / R - V_4 / R = I_4 + (V_3 - V_4) / R + (V_2 - V_4) / R = (2V_4 + V_3 + V_2) / R$

- B1P: $I_1 = I_{1P} + I_2 = BAT1 current$ $I_{1P} + I_{CB} = V1 / R \Rightarrow I_{1P} = V_1 / R - V_4 / R$ $I_1 = I_2 + V_1 / R - V_4 / R = I_4 + (V_3 - V_4) / R + (V_2 - V_4) / R + (V_1 - V_4) / R$ $= (V_4 + V_3 + V_2 + V_1) / R$
- when $V_1 = V_2 = V_3 = V4$, $I_{1P} = I_{2P} = I_{3P} = 0$ and $I_1 = I_2 = I_3 = I_4 = 4V_4 / R$.

Due to process variations, the MAX1665 does draw a minute current (70nA \sim 150nA) from the intermediate node even when the cells are matched. This current difference exists in the sampling mode, which is 1/32 of the whole time period, making the average of this current 2nA to 5nA.





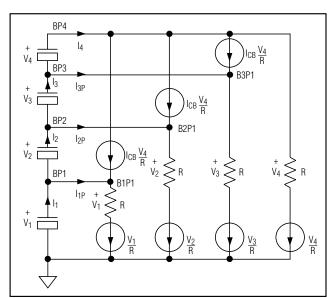


Figure 2. Sampling Mode Equivalent Circuit

Applications Information

Choosing an External MOSFET

The external N-channel MOSFETs act as gated switches to enable or disable the charging/discharging process. CHG and DSG control the gate of these external MOSFETs to prevent damage to the Li+ cells. For overcurrent conditions, the voltage at DSG equals the voltage at BN, thereby reducing all current flow, including the path through the body diode of the N-channel MOSFET. Note that the MAX1665X clamps the V_{GS} voltage to a maximum of 20V.

The IRF7101 is a low-cost, dual N-channel MOSFET that is available in a small 8-pin SO package. Depending on the maximum charge and discharge rates, use different MOSFETs to optimize each application. Table 3 summarizes recommended MOSFETs.

2, 3, and 4-Cell Applications

Figures 3 through 5 depict circuits for 2, 3, and 4-cell applications. Note that the two series MOSFETs (IRF7101 dual N-channel MOSFETs) are oriented to prevent body diode current flow. The indicated polarity symbols show the connection for the external source required to charge the Li+ cells. This external charger source also supplies the gate drive to the MOSFETs through pack + voltage / pack.

Table 3. Recommended MOSFETs

| DUAL N-CHANNEL MOSFETs | TYPICAL R _{DS(ON)} (Ω) | MAX V _{GS} (V) |
|---------------------------|------------------------------------|----------------------------|
| IRF9956 | 0.10 | ±20 |
| FDS6990A | 0.018 | ±20 |
| Si9936 | 0.050 | ±20 |

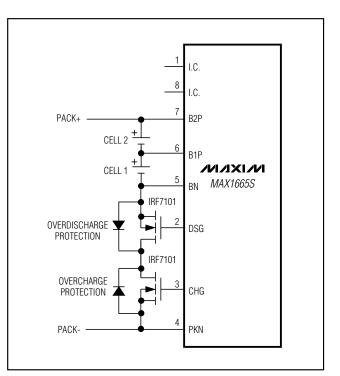


Figure 3. Typical 2-Cell Operating Circuit

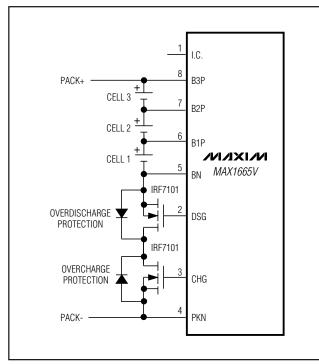


Figure 4. Typical 3-Cell Operating Circuit

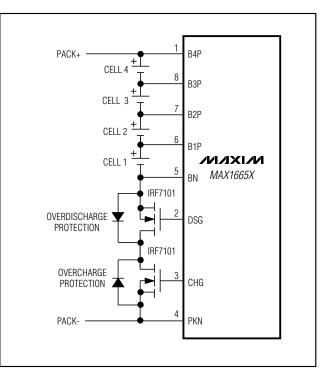
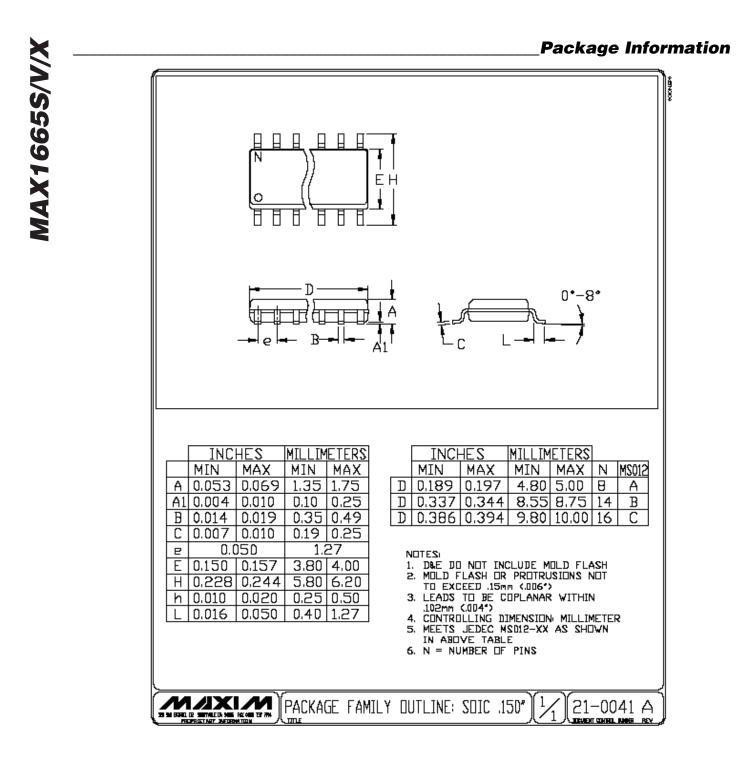


Figure 5. Typical 4-Cell Operating Circuit

MAX1665S/V/X



NOTES

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NOTES

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